

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising a thin film integrated circuit,

wherein the thin film integrated circuit comprises:

a substrate;

an adhesive over the substrate;

a metal oxide over the adhesive;

an insulating film over the metal oxide;

a memory comprising a first semiconductor film ~~[[over]]~~ on and in contact with the insulating film;

a transistor comprising a second semiconductor film, a gate insulating film, and a gate electrode ~~which are provided over~~ electrode, wherein the second semiconductor film is formed on and in contact with the insulating film.

2. (Previously Presented) A semiconductor device according to claim 1, wherein the metal oxide comprises WO_2 or WO_3 .

3. (Previously Presented) A semiconductor device according to claim 1, wherein the metal oxide is an oxide of an element selected from the group consisting of W, Ti, Ta, Mo, Nd, Ni, Co, Zr, Zn, Ru, Rh, Pd, Os, and Ir; an alloy containing the metal as a main component; or a chemical compound thereof.

4. (Previously Presented) A semiconductor device according to claim 1, wherein the first semiconductor film functions as an active region.

5. (Previously Presented) A semiconductor device according to claim 1, wherein the first semiconductor film functions as a channel region.

6. (Currently Amended) An IC label comprising a thin film integrated circuit, wherein the thin film integrated circuit comprises:

a substrate;

an adhesive over the substrate;

a metal oxide over the adhesive;

an insulating film over the metal oxide;

a memory comprising a first semiconductor film ~~[[over]]~~ on and in contact with the insulating film;

a transistor comprising a second semiconductor film, a gate insulating film, and a gate ~~electrode which are provided over electrode,~~ wherein the second semiconductor film is formed on and in contact with the insulating film.

7. (Original) An IC label according to claim 6, wherein the IC label is a contactless type.

8. (Previously Presented) An IC label according to claim 6, wherein a surface of the IC label can be printed with a character, a letter, text, a symbol, or a diagram.

9. (Currently Amended) An IC label comprising a contactless thin film integrated circuit,

wherein the thin film integrated circuit comprises:

a substrate;

an adhesive over the substrate;

a metal oxide over the adhesive;

an insulating film over the metal oxide;
a semiconductor film provided over the insulating film;
a gate electrode provided over the semiconductor film with a gate insulating film interposed between the semiconductor layer and the gate electrode; and
an antenna formed from the same material as the gate electrode,
wherein the antenna is formed on and in contact with the gate insulating film.

10. (Canceled)

11. (Original) An IC label according to claim 9, wherein the antenna comprises a conductive paste.

12. (Previously Presented) An IC label comprising a contactless thin film integrated circuit,

wherein the thin film integrated circuit comprises:

a substrate;
an adhesive over the substrate;
a metal oxide over the adhesive;
an insulating film over the metal oxide;
a transistor comprising a semiconductor film, a gate insulating film, and a gate electrode which are provided over the insulating film;
an interlayer insulating film over the transistor;
a wiring formed on the interlayer insulating film, wherein the wiring is connected to an impurity region of the semiconductor film; and
an antenna formed on the interlayer insulating film.

13. (Previously Presented) An IC label according to claim 12, wherein the antenna comprises a same material as the wiring.

14. (Original) An IC label according to claim 12, wherein the antenna comprises a conductive paste.

15. (Currently Amended) A container comprising a thin film integrated circuit, wherein the thin film integrated circuit comprises:

a substrate;

an adhesive over the substrate;

a metal oxide over the adhesive;

an insulating film over the metal oxide;

a memory comprising a first semiconductor film ~~[[over]]~~ on and in contact with the insulating film;

a transistor comprising a second semiconductor film, a gate insulating film, and a gate electrode, ~~which are provided over~~ wherein the second semiconductor film is formed on and in contact with the insulating film.

16. (Original) A container according to claim 15, wherein the thin film integrated circuit is covered by a label.

17. (Original) A container according to claim 16, wherein a protective film having a DLC film or a CN film is provided between the thin film integrated circuit and the label.

18. (Original) A container according to claim 15, wherein the thin film integrated circuit is held between a first label and a second label, and the second label is affixed to the thin film integrated circuit with an adhesive agent.

19. (Previously Presented) A container according to claim 15, wherein the metal oxide is adhered to the container.

20. (Currently Amended) A container comprising a contactless thin film integrated circuit,

wherein the thin film integrated circuit comprises:

a substrate;

an adhesive over the substrate;

a metal oxide over the adhesive;

an insulating film over the metal oxide;

a semiconductor film provided over the insulating film;

a gate electrode that is provided over the semiconductor film with a gate insulating film interposed between the semiconductor layer and the gate electrode; and

an antenna formed from the same material as the gate electrode,

wherein the antenna is formed on and in contact with the gate insulating film.

21. (Original) A container according to claim 20, wherein the thin film integrated circuit is covered by a label.

22. (Original) A container according to claim 21, wherein a protective film having a DLC film or a CN film is provided between the thin film integrated circuit and the label.

23. (Original) A container according to claim 20, wherein the thin film integrated circuit is held between a first label and a second label, and the second label is affixed to the thin film integrated circuit with an adhesive agent.

24. (Previously Presented) A container comprising a contactless thin film integrated circuit,

wherein the thin film integrated circuit comprises:

a substrate;

an adhesive over the substrate;
a metal oxide over the adhesive;
an insulating film over the metal oxide;
a transistor comprising a semiconductor film, a gate insulating film, and a gate electrode which are provided over the insulating film;
an interlayer insulating film over the transistor;
a wiring provided on the interlayer insulating film; and
an antenna provided on the interlayer insulating film.

25. (Original) A container according to claim 24, wherein the thin film integrated circuit is covered by a label.

26. (Original) A container according to claim 25, wherein a protective film having a DLC film or a CN film is provided between the thin film integrated circuit and the label.

27. (Original) A container according to claim 24, wherein the thin film integrated circuit is held between a first label and a second label, and the second label is affixed to the thin film integrated circuit with an adhesive agent.

28.-62. (Canceled)